

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 63-060189

(43)Date of publication of application : 16.03.1988

(51)Int.Cl.

C30B 15/02
C30B 15/30
// H01L 21/18

(21)Application number : 61-202495

(71)Applicant : TOSHIBA CORP

(22)Date of filing : 28.08.1986

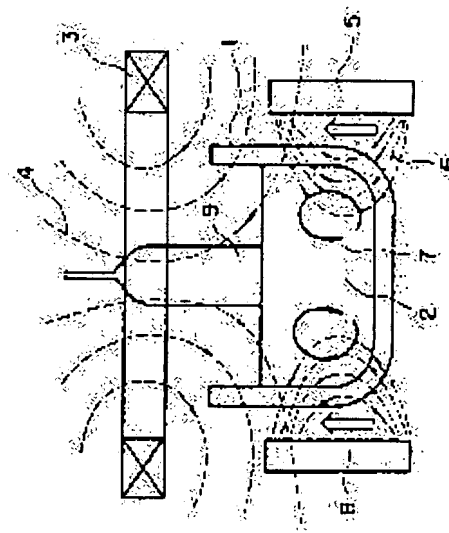
(72)Inventor : YAMAZAKI HIDEKI

(54) PRODUCTION OF SEMICONDUCTOR SINGLE CRYSTAL

(57)Abstract:

PURPOSE: To obtain the title single crystal without any crystal defect and further having an excellent concn. distribution by pulling up a single crystal while impressing a stationary magnetic field in the vicinity of the solidified interface of a melt and impressing a shifting magnetic field or rotating magnetic field by a low frequency on the intermediate and lower parts at the time of producing a semiconductor single crystal by a pull method.

CONSTITUTION: The semiconductor single crystal 9 is pulled up from the surface of a raw material melt 2 in a crucible 1, and produced. In this case, the stationary magnetic field 4 (generated by passing a DC current through a magnet 3) is impressed in the vicinity of the solidified interface of the melt 2 to control the oscillation around the interface of the melt 2, the shifting magnetic field 6 (by a magnet 5) or the rotating magnetic field by low frequency is impressed on the intermediate and lower parts, and the crystal is pulled up while generating vertical oscillation (an agitation current 7) in the melt 2.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]